Is Now Part of

ON Semiconductor®

To learn more about ON Semiconductor, please visit our website at
www.onsemi.com

Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (_), the underscore (_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.onsemi.com. Please email any questions regarding the system integration to Fairchild_questions@onsemi.com.

January 2016

FJBE2150D
ESBC™ Rated NPN Silicon Transistor

ESBC Features (FDC655 MOSFET)

$V_{CS(ON)}$	I_C	Equiv. $R_{CS(ON)}$
0.131 V	0.5 A	0.261 Ω(1)

- Low Equivalent On Resistance
- Very Fast Switch: 150 kHz
- Squared RBSOA: Up to 1500 V
- Avalanche Rated
- Low Driving Capacitance, No Miller Capacitance (Typ. 12 pF Capacitance at 200 V)
- Low Switching Losses
- Reliable HV Switch: No False Triggering due to High dv/dt Transients

Applications

- High-Voltage and High-Speed Power Switches
- Emitter-Switched Bipolar/MOSFET Cascode (ESBC™)
- Smart Meters, Smart Breakers, HV Industrial Power Supplies
- Motor Drivers and Ignition Drivers

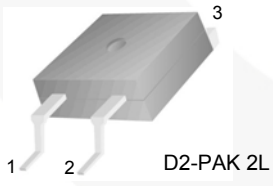
Description

The FJBE2150D is a low-cost, high-performance power switch designed to be used in an ESBC™ configuration in applications such as: power supplies, motor drivers, smart grid, or ignition switches. The power switch is designed to operate up to 1500 volts and up to 3 amps, while providing exceptionally low on-resistance and very low switching losses.

The ESBC™ switch is designed to be driven using off-the-shelf power supply controllers or drivers. The ESBC™ MOSFET is a low-voltage, low-cost, surface-mount device that combines low-input capacitance and fast switching. The ESBC™ configuration further minimizes the required driving power because it does not have Miller capacitance.

The FJBE2150D provides exceptional reliability and a large operating range due to its square Reverse-Bias-Safe-Operating-Area (RBSOA) and rugged design. The device is avalanche rated and has no parasitic transistors, so is not prone to static dv/dt failures.

The power switch is manufactured using a dedicated high-voltage bipolar process and is packaged in high-voltage HV-D2PAK rated at 2500 V creepage and clearance.



1.Base 2.Emitter 3.Collector

Figure 1. Pin Configuration

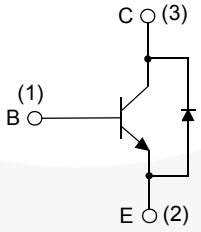


Figure 2. Internal Schematic Diagram

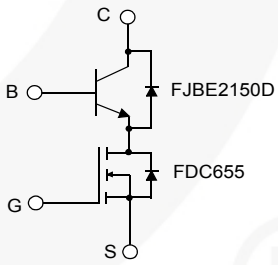


Figure 3. ESBC Configuration(2)

Ordering Information

Part Number	Marking	Package	Packing Method
FJBE2150DTU	J2150D	D2-PAK 2L (TO-263 2L)	Tube

Notes:

1. Figure of Merit.
2. Other Fairchild MOSFETs can be used in this ESBC application.

Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. Values are at T_A = 25°C unless otherwise noted.

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	1500	V
V_{CEO}	Collector-Emitter Voltage	800	V
V_{EBO}	Emitter-Base Voltage	12	V
I_C	Collector Current	2	A
I_{CP}	Collector Current (Pulse)	3	A
I_B	Base Current	1	A
I_{BP}	Base Current (Pulse)	2	A
P_D	Power Dissipation (T_C = 25°C)	110	W
T_J	Operating and Junction Temperature Range	- 55 to +125	°C
T_{STG}	Storage Temperature Range	- 65 to +150	°C
EAS	Avalanche Energy (T_J = 25°C, 8 mH)	3.5	mJ

Thermal Characteristics[3]

Values are at T_A = 25°C unless otherwise noted.

Symbol	Parameter	Max.	Unit
$R_{\theta jc}$	Thermal Resistance, Junction to Case	1.13	°C/W
$R_{\theta ja}$	Thermal Resistance, Junction to Ambient	76.42	°C/W

Note:

3. Device mounted on FR-4 PCB, board size = 76.2 mm x 114.3 mm, land pattern 12.70 mm x 9.45 mm, trace size = 10 mil.

Electrical Characteristics[4]

Values are at T_A = 25°C unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{CBO}	Collector-Base Breakdown Voltage	I_C = 0.5 mA, I_E = 0	1500	1689		V
BV_{CEO}	Collector-Emitter Breakdown Voltage	I_C = 5 mA, I_B = 0	800	870		V
BV_{EBO}	Emitter-Base Breakdown Voltage	I_E = 0.5 mA, I_C = 0	12.0	14.8		V
I_{CES}	Collector Cut-off Current	V_{CE} = 1500 V, V_{BE} = 0		0.01	100	μA
I_{CEO}	Collector Cut-off Current	V_{CE} = 800 V, I_B = 0		0.01	100	μA
I_{EBO}	Emitter Cut-off Current	V_{EB} = 12 V, I_C = 0		0.05	500	μA
h_{FE}	DC Current Gain	V_{CE} = 3 V, I_C = 0.4 A	20	29	35	
		V_{CE} = 10 V, I_C = 5 mA	20	43		
V_{CE}(sat)	Collector-Emitter Saturation Voltage	I_C = 0.25 A, I_B = 0.05 A		0.16		V
		I_C = 0.5 A, I_B = 0.167 A		0.12		
		I_C = 1 A, I_B = 0.33 A		0.25		
V_{BE}(sat)	Base-Emitter Saturation Voltage	I_C = 500 mA, I_B = 50 mA		0.74	1.20	V
		I_C = 2 A, I_B = 0.4 A		0.85	1.20	
C_{IB}	Input Capacitance	V_{EB} = 10 V, I_C = 0, f = 1 MHz		745	1000	pF
C_{OB}	Output Capacitance	V_{CB} = 200 V, I_E = 0, f = 1 MHz		15		pF
f_T	Current Gain Bandwidth Product	I_C = 0.1 A, V_{CE} = 10 V		5		MHz
V_F	Diode Forward Voltage	I_F = 0.4 A		0.76	1.20	V
		I_F = 1 A		0.83	1.50	

Note:

4. Pulse test: pulse width = 20 μs, duty cycle≤ 10%.

ESBC Configured Electrical Characteristics(5)

Values are at T_A = 25°C unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
f_T	Current Gain Bandwidth Product	I_C = 0.1 A,V_{CE} = 10 V		25		MHz
It_f	Inductive Current Fall Time	V_{GS} = 10 V, R_G = 47 Ω, V_{Clamp} = 500 V, t_p = 3.1 µs, I_C = 0.3 A, I_B = 0.03 A, L_C = 1 mH, SRF = 480 kHz		137		ns
t_s	Inductive Storage Time			350		ns
Vt_f	Inductive Voltage Fall Time			120		ns
Vt_r	Inductive Voltage Rise Time			100		ns
t_c	Inductive Crossover Time			137		ns
It_f	Inductive Current Fall Time	V_{GS} = 10 V, R_G = 47 Ω, V_{Clamp} = 500 V, t_p = 10 µs, I_C = 1 A, I_B = 0.2 A, L_C = 1 mH, SRF = 480 kHz		35		ns
t_s	Inductive Storage Time			980		ns
Vt_f	Inductive Voltage Fall Time			30		ns
Vt_r	Inductive Voltage Rise Time			195		ns
t_c	Inductive Crossover Time			210		ns
V_{CSW}	Maximum Collector Source Voltage at Turn-off without Snubber	h_{FE} = 5, I_C = 2 A	1500			V
$I_{GS(OS)}$	Gate-Source Leakage Current	V_{GS} = ±20 V		1.0		nA
$V_{CS(ON)}$	Collector-Source On Voltage	V_{GS} = 10 V, I_C = 2 A, I_B = 0.67 A, h_{FE} = 3		2.210		V
		V_{GS} = 10 V, I_C = 1 A, I_B = 0.33 A, h_{FE} = 3		0.321		
		V_{GS} = 10 V, I_C = 0.5 A, I_B = 0.17 A, h_{FE} = 3		0.131		
		V_{GS} = 10 V, I_C = 0.3 A, I_B = 0.06 A, h_{FE} = 5		0.166		
$V_{GS(th)}$	Gate Threshold Voltage	V_{BS} = V_{GS}, I_B = 250 µA		1.9		V
C_{iss}	Input Capacitance (V_{GS} = V_{CB} = 0)	V_{CS} = 25 V, f = 1 MHz		470		pF
$Q_{GS(tot)}$	Gate-Source Charge V_{CB} = 0	V_{GS} = 10 V, I_C = 8 A, V_{CS} = 25 V		9		nC
$r_{DS(ON)}$	Static Drain-Source On Resistance	V_{GS} = 10 V, I_D = 6.3 A		21		mΩ
		V_{GS} = 4.5 V, I_D = 5.5 A		26		
		V_{GS} = 10 V, I_D = 6.3 A, T_J = 125°C		30		

Note:

5. Used typical FDC655 MOSFET values in table. Values can vary if other Fairchild MOSFETs are used.

Typical Performance Characteristics

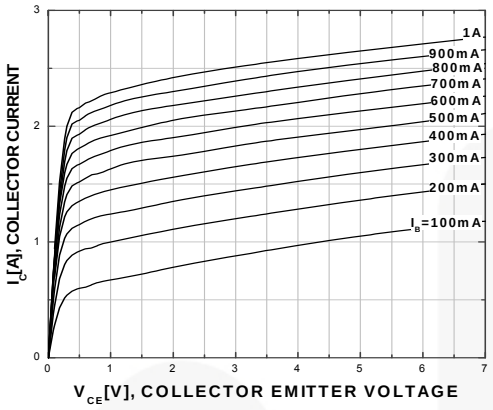


Figure 4. Static Characteristic

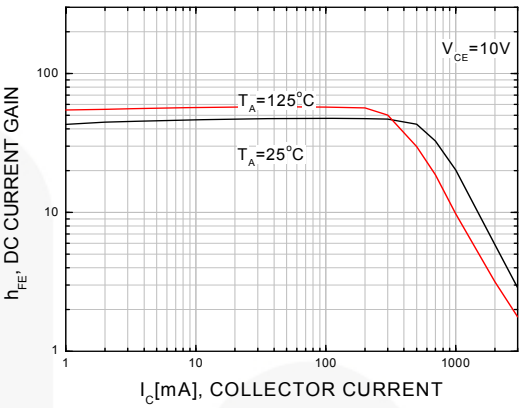


Figure 5. DC Current Gain

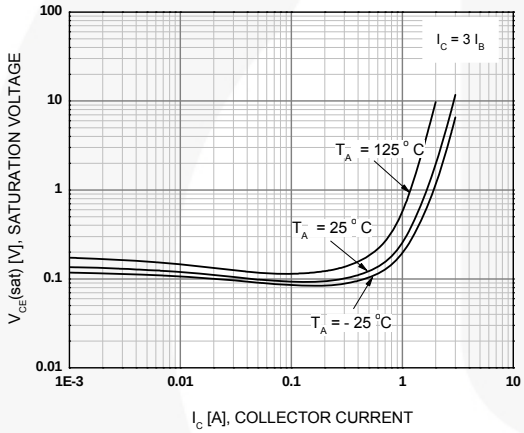


Figure 6. Collector-Emitter Saturation Voltage
h_{FE} = 3

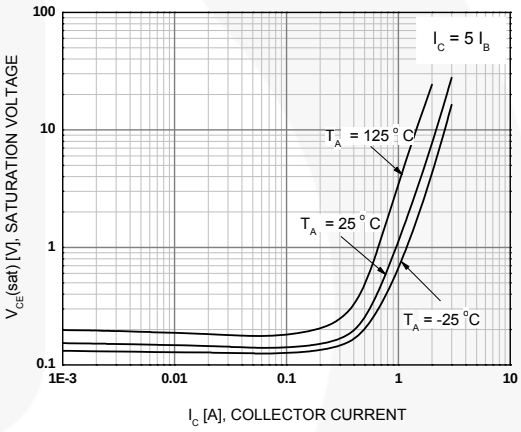


Figure 7. Collector-Emitter Saturation Voltage
h_{FE} = 5

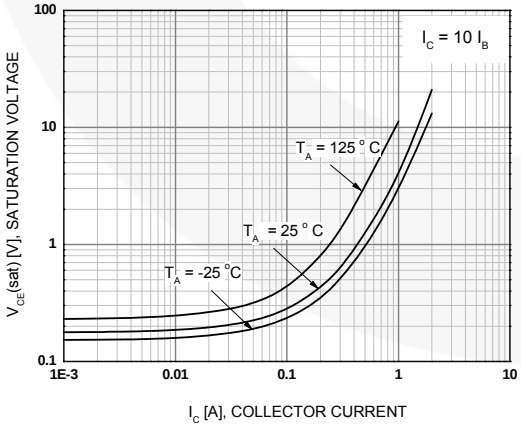


Figure 8. Collector-Emitter Saturation Voltage
h_{FE} = 10

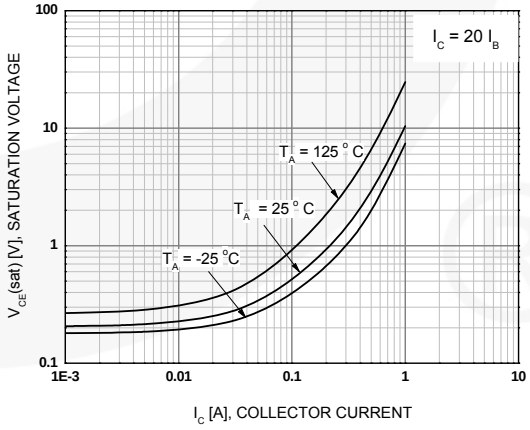


Figure 9. Collector-Emitter Saturation Voltage
h_{FE} = 20

Typical Performance Characteristics (Continued)

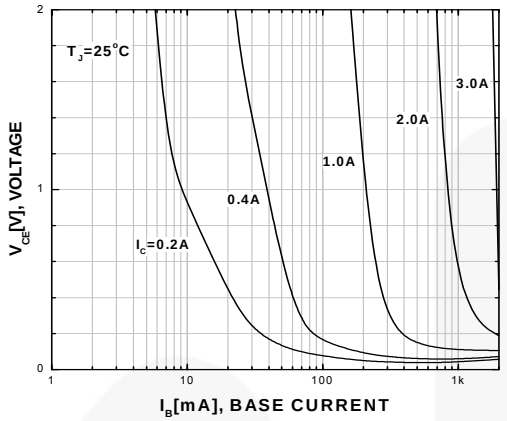


Figure 10. Typical Collector Saturation Voltage

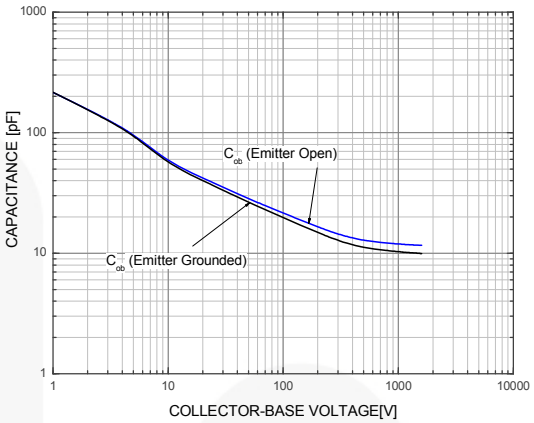


Figure 11. Capacitance

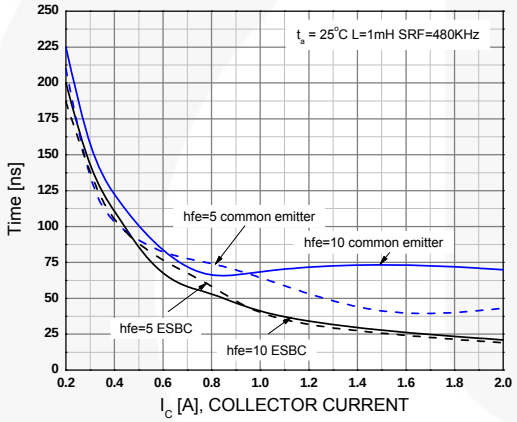


Figure 12. Inductive Load Collector Current Fall-Time (t_f)

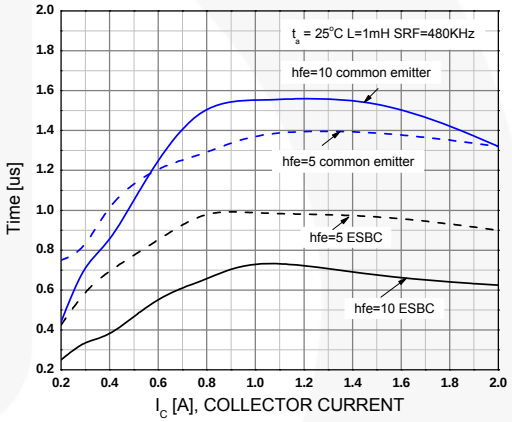


Figure 13. Inductive Load Collector Current Storage Time (t_{stg})

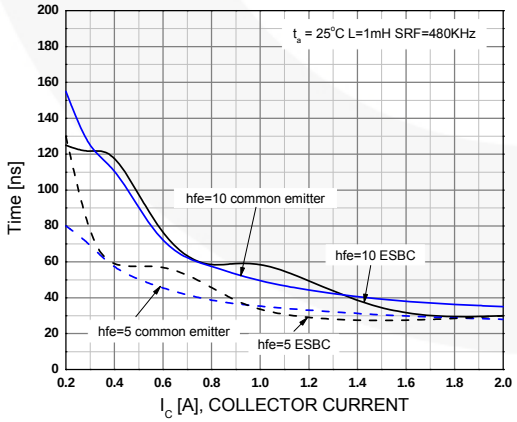


Figure 14. Inductive Load Collector Voltage Fall-Time (t_f)

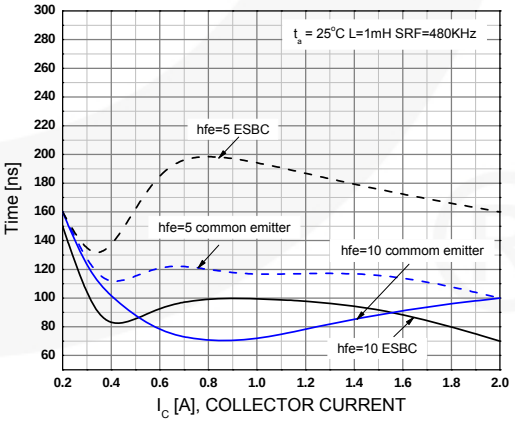


Figure 15. Inductive Load Collector Voltage Rise-Time (t_r)

Typical Performance Characteristics (Continued)

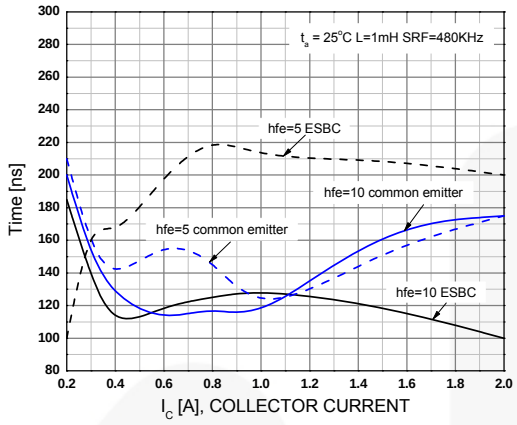


Figure 16. Inductive Load Collector Current / Voltage Crossover (t_c)

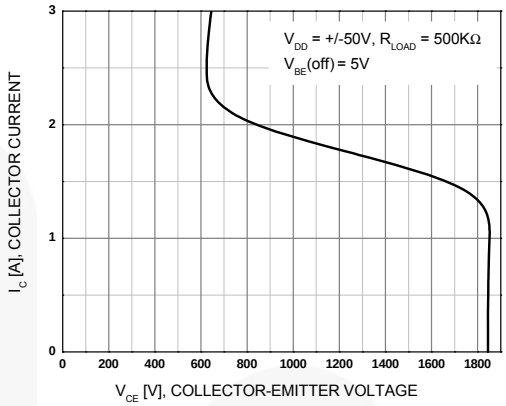


Figure 17. BJT Reverse Bias Safe Operating Area

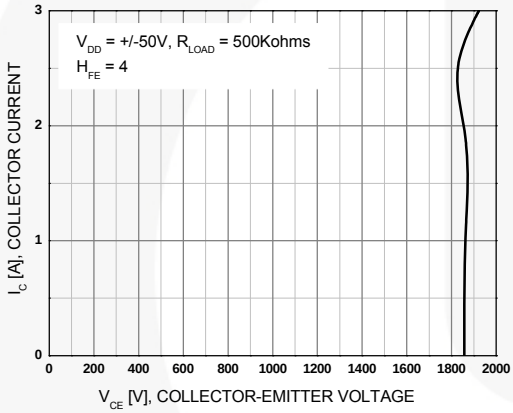


Figure 18. ESBC RBSOA

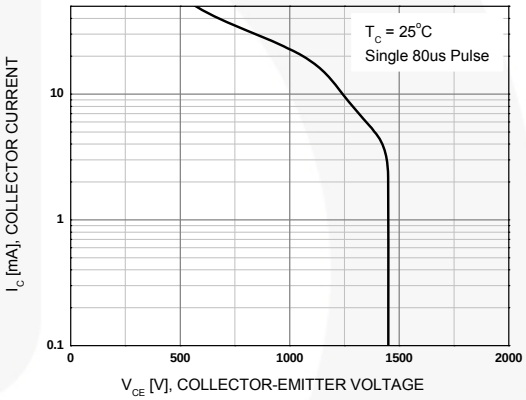


Figure 19. Crossover Forward Bias Safe Operating Area (FBSOA)

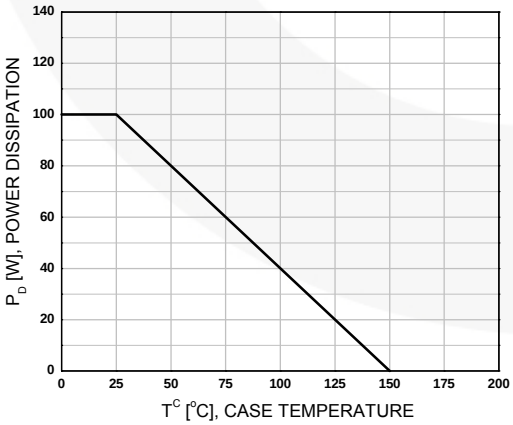


Figure 20. Power Derating

Test Circuits

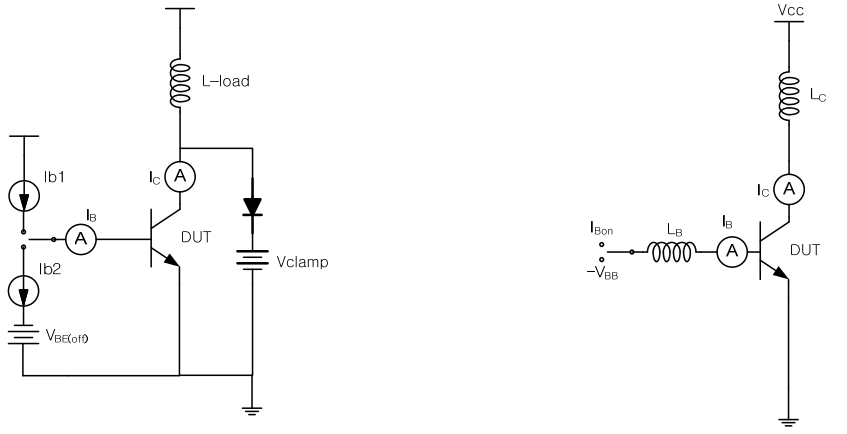


Figure 21. Test Circuit for Inductive Load and Reverse Bias Safe Operating

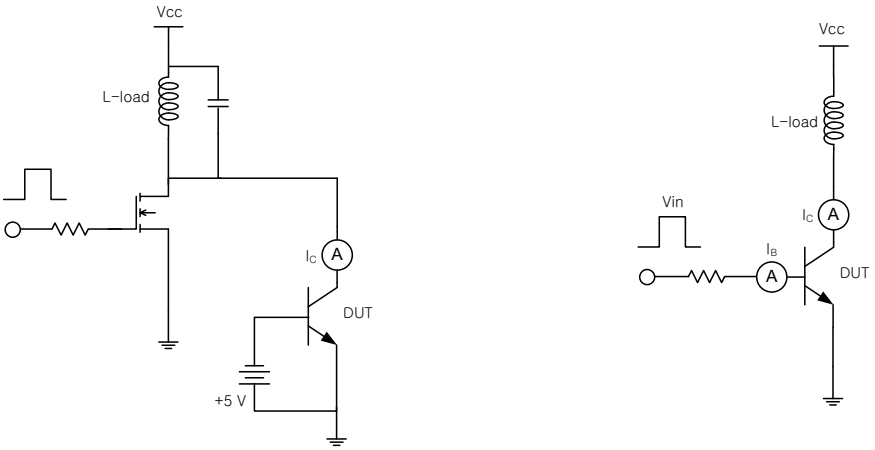


Figure 22. Energy Rating Test Circuit

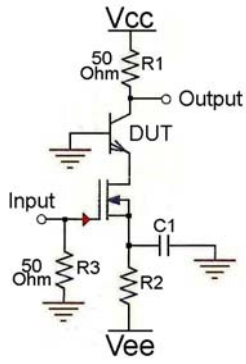


Figure 23. f_T Measurement

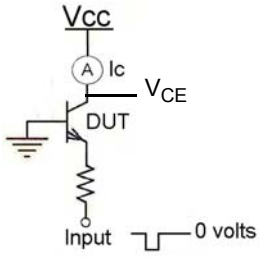


Figure 24. FBSOA

Test Circuits (Continued)

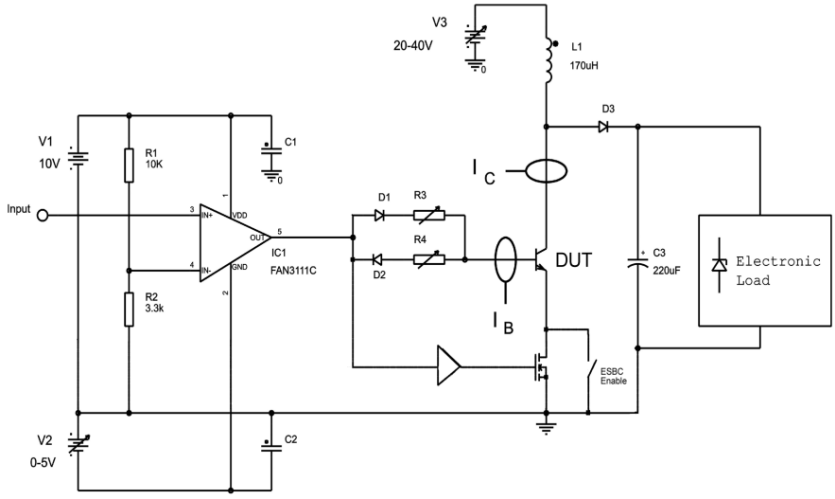


Figure 25. Simplified Saturated Switch Driver Circuit

Functional Test Waveforms

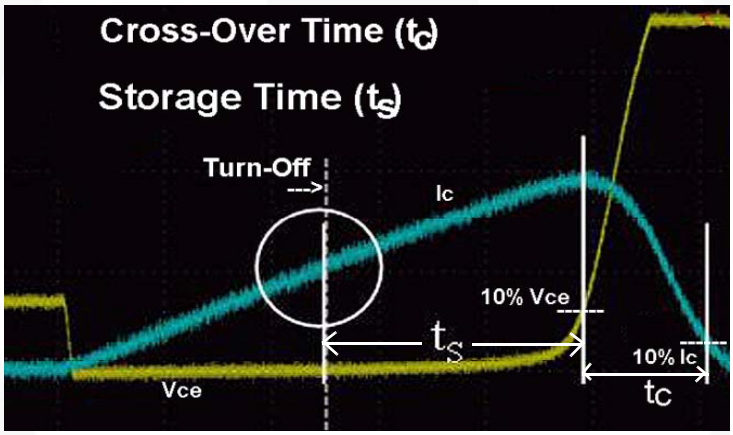


Figure 26. Crossover Time Measurement

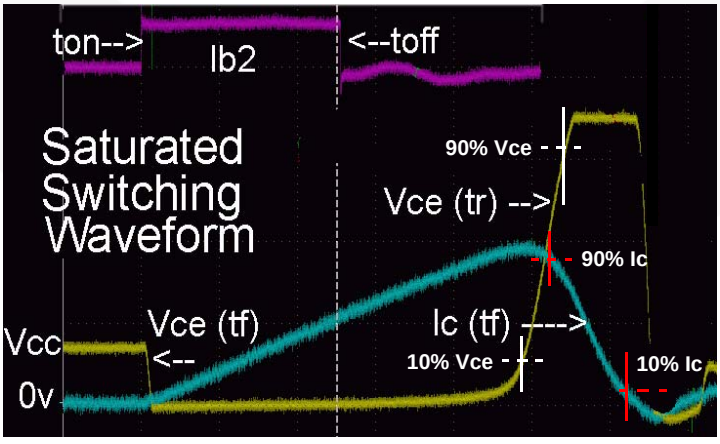


Figure 27. Saturated Switching Waveform

Functional Test Waveforms (Continued)

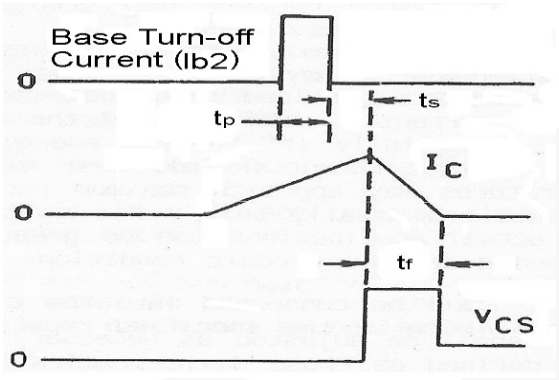


Figure 28. Storage Time - Common Emitter Base Turn-off (Ib2) to I_C Fall-Time

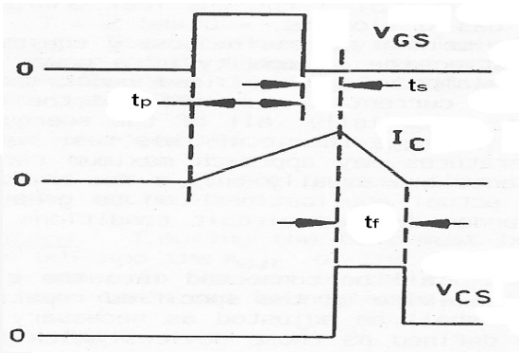


Figure 29. Storage Time - ESBC FET Gate (off) to I_C Fall-Time

Very Wide Input Voltage Range Supply

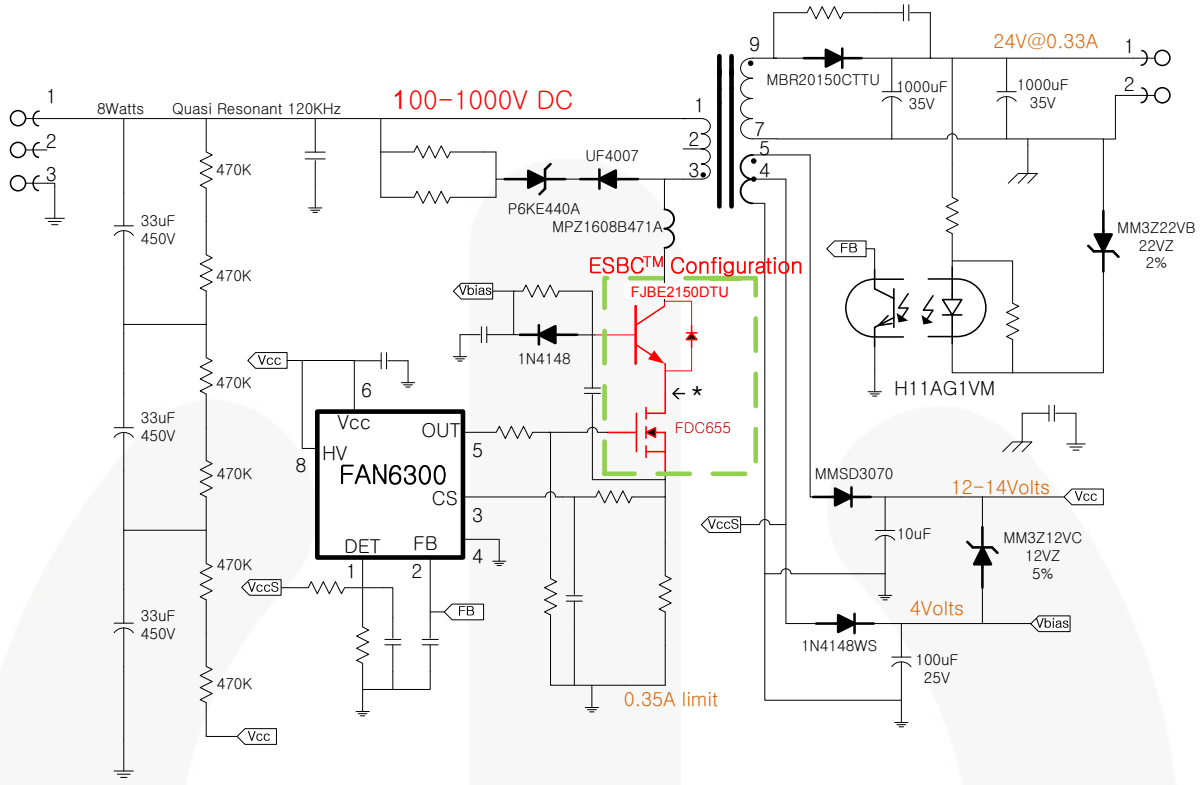


Figure 30. 8 W; Secondary-Side Regulation: 3 Capacitor Input; Quasi Resonant

Driving ESBC Switches

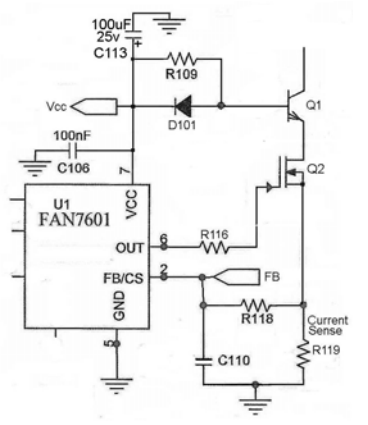


Figure 31. V_{CC} Derived

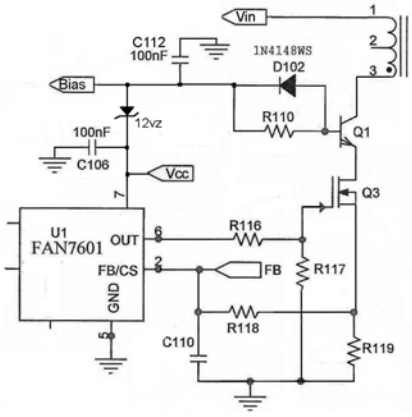


Figure 32. V_{bias} Supply Derived

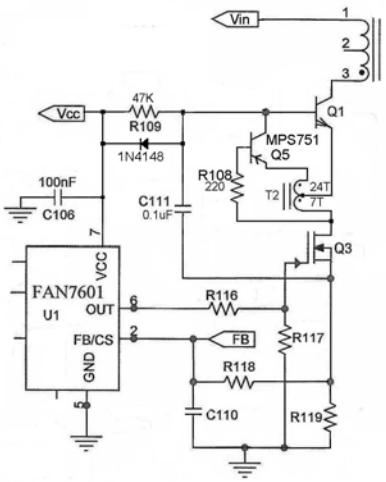


Figure 33. Proportional Drive

Physical Dimensions

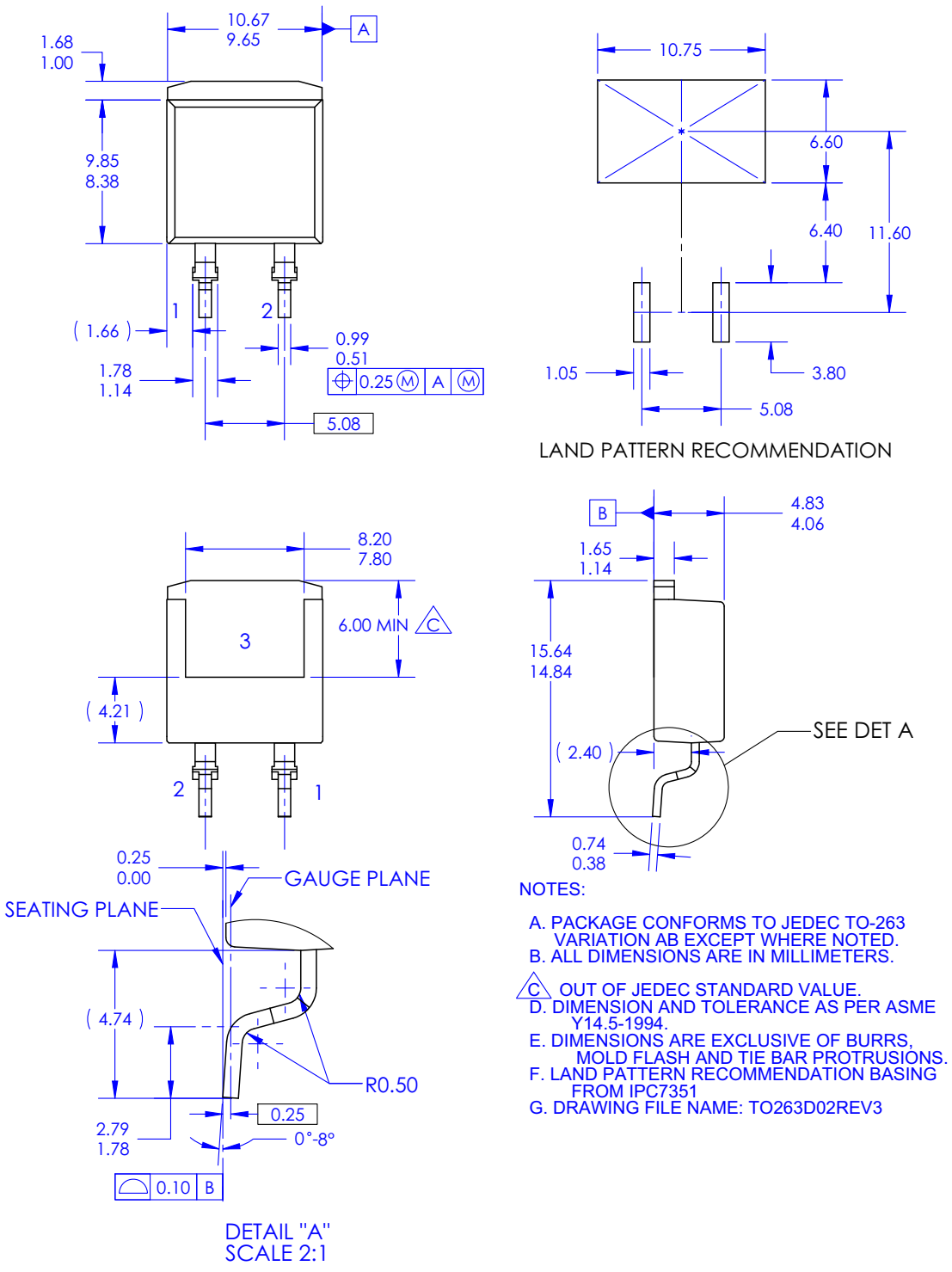


Figure 34. 2 LEAD, TO-263, JEDEC TO263 VARIATION AB, D2PAK

TRADEMARKS

The following includes registered and unregistered trademarks and service marks, owned by Fairchild Semiconductor and/or its global subsidiaries, and is not intended to be an exhaustive list of all such trademarks.

AccuPower™
AttitudeEngine™
Awinda®
AX-CAP®*
BitSiC™
Build it Now™
CorePLUS™
CorePOWER™
CROSSVOLT™
CTL™
Current Transfer Logic™
DEUXPEED®
Dual Cool™
EcoSPARK®
EfficientMax™
ESBC™
F®
Fairchild®
Fairchild Semiconductor®
FACT Quiet Series™
FACT®
FastvCore™
FETBench™
FPS™
F-PFS™
FRFET®
Global Power Resource SM
GreenBridge™
Green FPS™
Green FPS™ e-Series™
G*max*™
GTO™
IntelliMAX™
ISOPLANAR™
Making Small Speakers Sound Louder and Better™
MegaBuck™
MICROCOUPLER™
MicroFET™
MicroPak™
MicroPak2™
MillerDrive™
MotionMax™
MotionGrid®
MTi®
MTx®
MVN®
mWSaver®
OptoHiT™
OPTOLOGIC®
OPTOPLANAR®
®
Power Supply WebDesigner™
PowerTrench®
PowerXS™
Programmable Active Droop™
QFET®
QS™
Quiet Series™
RapidConfigure™
™
Saving our world, 1mW/W/kW at a time™
SignalWise™
SmartMax™
SMART START™
Solutions for Your Success™
SPM®
STEALTH™
SuperFET®
SuperSOT™-3
SuperSOT™-6
SuperSOT™-8
SupreMOS®
SyncFET™
Sync-Lock™
SYSTEM GENERAL®*
TinyBoost®
TinyBuck®
TinyCalc™
TinyLogic®
TINYOPTO™
TinyPower™
TinyPWM™
TinyWire™
TranSiC™
TriFault Detect™
TRUECURRENT®*
μSerDes™
SerDes™
UHC®
Ultra FRFET™
UniFET™
VCX™
VisualMax™
VoltagePlus™
XS™
Xsens™
仙童®

* Trademarks of System General Corporation, used under license by Fairchild Semiconductor.

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION, OR DESIGN. TO OBTAIN THE LATEST, MOST UP-TO-DATE DATASHEET AND PRODUCT INFORMATION, VISIT OUR WEBSITE AT HTTP://WWW.FAIRCHILDSEMI.COM. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN, WHICH COVERS THESE PRODUCTS.

AUTHORIZED USE

Unless otherwise specified in this data sheet, this product is a standard commercial product and is not intended for use in applications that require extraordinary levels of quality and reliability. This product may not be used in the following applications, unless specifically approved in writing by a Fairchild officer: (1) automotive or other transportation, (2) military/aerospace, (3) any safety critical application – including life critical medical equipment – where the failure of the Fairchild product reasonably would be expected to result in personal injury, death or property damage. Customer's use of this product is subject to agreement of this Authorized Use policy. In the event of an unauthorized use of Fairchild's product, Fairchild accepts no liability in the event of product failure. In other respects, this product shall be subject to Fairchild's Worldwide Terms and Conditions of Sale, unless a separate agreement has been signed by both Parties.

ANTI-COUNTERFEITING POLICY

Fairchild Semiconductor Corporation's Anti-Counterfeiting Policy. Fairchild's Anti-Counterfeiting Policy is also stated on our external website, www.fairchildsemi.com, under Terms of Use

Counterfeiting of semiconductor parts is a growing problem in the industry. All manufacturers of semiconductor products are experiencing counterfeiting of their parts. Customers who inadvertently purchase counterfeit parts experience many problems such as loss of brand reputation, substandard performance, failed applications, and increased cost of production and manufacturing delays. Fairchild is taking strong measures to protect ourselves and our customers from the proliferation of counterfeit parts. Fairchild strongly encourages customers to purchase Fairchild parts either directly from Fairchild or from Authorized Fairchild Distributors who are listed by country on our web page cited above. Products customers buy either from Fairchild directly or from Authorized Fairchild Distributors are genuine parts, have full traceability, meet Fairchild's quality standards for handling and storage and provide access to Fairchild's full range of up-to-date technical and product information. Fairchild and our Authorized Distributors will stand behind all warranties and will appropriately address any warranty issues that may arise. Fairchild will not provide any warranty coverage or other assistance for parts bought from Unauthorized Sources. Fairchild is committed to combat this global problem and encourage our customers to do their part in stopping this practice by buying direct or from authorized distributors.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.

Rev. I77

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA
Phone: 303−675−2175 or 800−344−3860 Toll Free USA/Canada
Fax: 303−675−2176 or 800−344−3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800−282−9855 Toll Free USA/Canada
Europe, Middle East and Africa Technical Support:
Phone: 421 33 790 2910
Japan Customer Focus Center
Phone: 81−3−5817−1050

ON Semiconductor Website: **www.onsemi.com**

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative